


Sal D9 33. (Amended) A process for depositing a tungsten silicide film on a substrate consisting essentially of:
depositing a discontinuous nucleation layer of tungsten silicide (WSi_x) on the substrate using a (CVD) process with a silane (SiH₄) silicon source gas and a reactant gas;
depositing a film of tungsten silicide (WSi_x) on the discontinuous nucleation layer using a (CVD) process by switching to dichlorosilane (SiH₂Cl₂) as a silicon source gas such that the dichlorosilane gas reacts with the reactant gas to form the tungsten silicide film; and
wherein said depositing said discontinuous nucleation layer of tungsten silicide and said depositing said film of tungsten silicide occur at a substantially equivalent temperature.

REMARKS

No new matter has been added. The Applicant requests entry of the foregoing amendment prior to examination of the application on the merits.

Respectfully submitted,



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Date: March 28, 2000

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